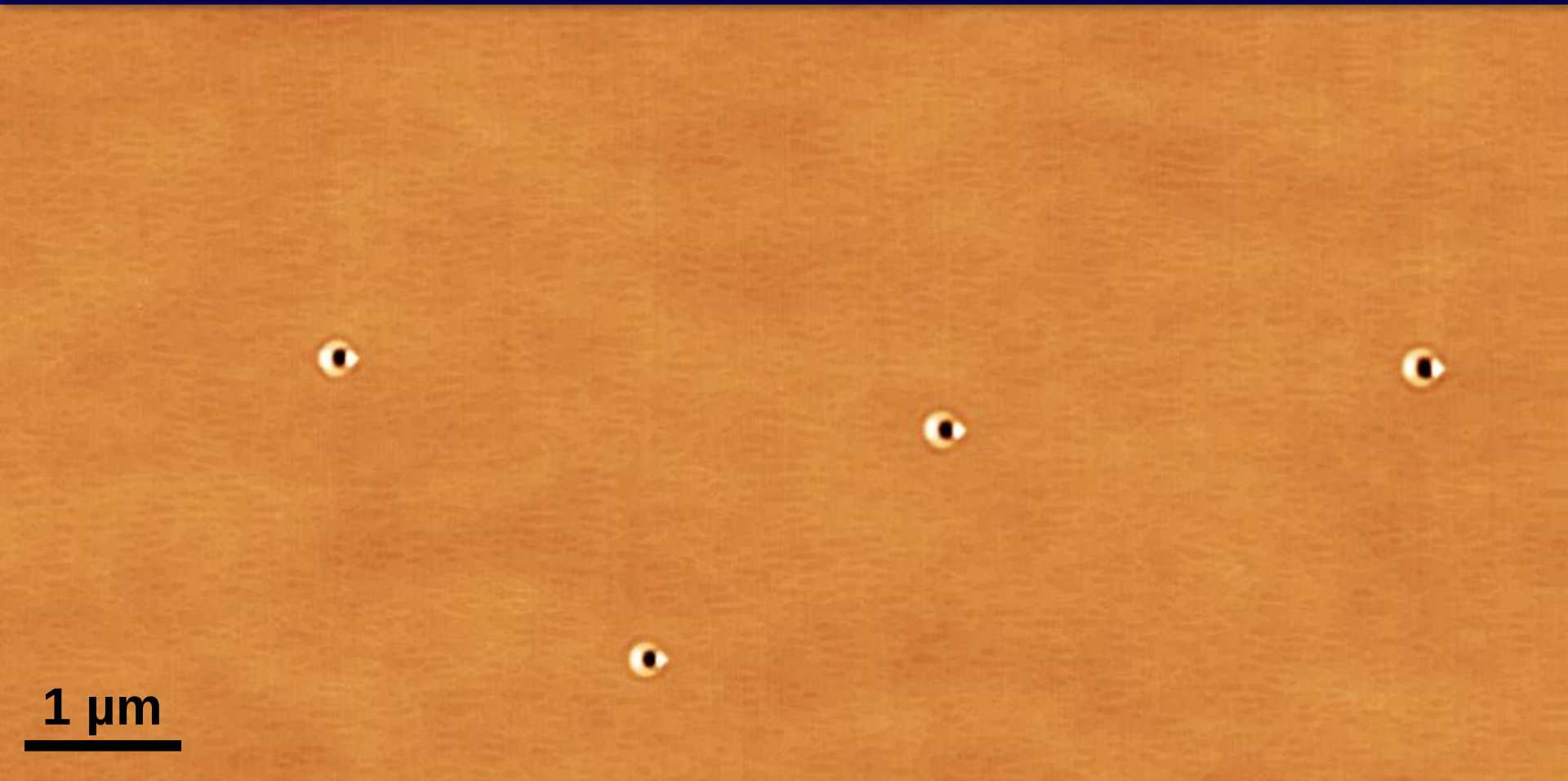
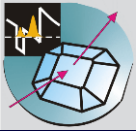


Self-assembled Droplet Etching for versatile Quantum Structures

Ch. Heyn, L. Ranasinghe, K. Denecke, S. Federsen, and W. Hansen
CHyN, University of Hamburg

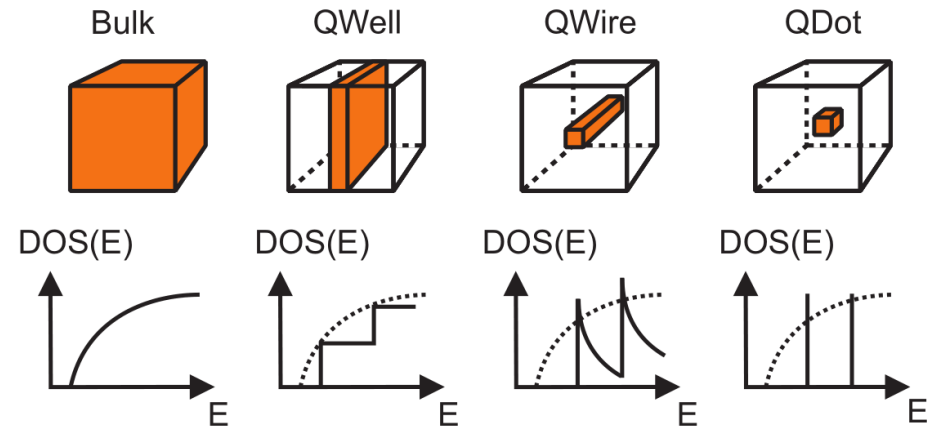


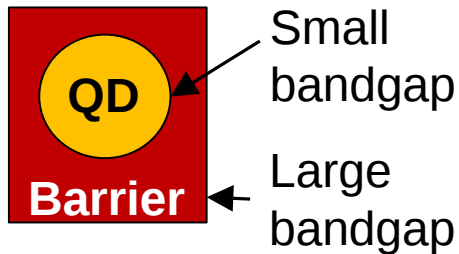
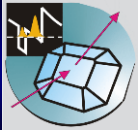


Small
bandgap

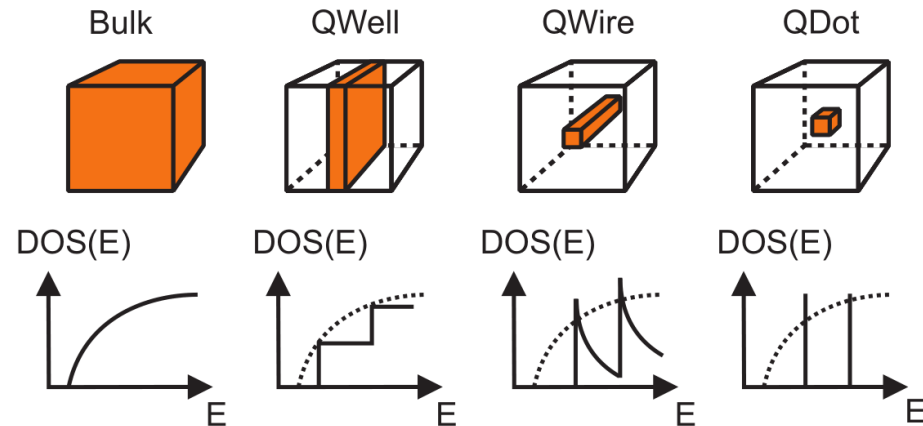
Large
bandgap

Size $\lesssim 50$ nm:
atom-like
0D density
of states





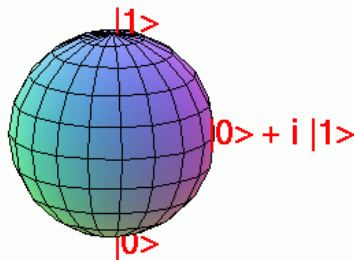
Size $\lesssim 50$ nm:
atom-like
0D density
of states



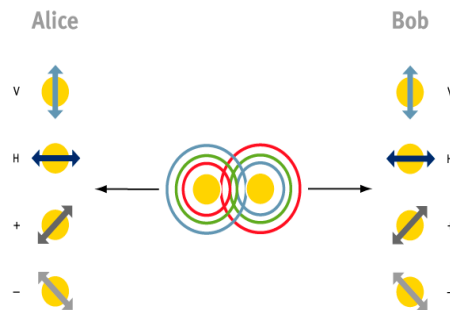
Applications

- **Laser, Solar cells:** dense QD ensembles
- **Quantum information:** single QDs

QuBits for
quantum
computing



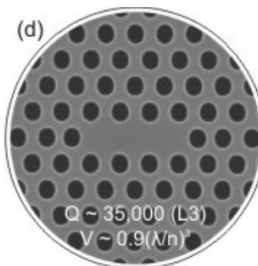
**Entangled
photons**
for quantum
cryptography



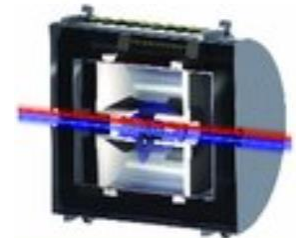
**Quantum
sensors,
....**

- **Integration:**

Photonic environment
Quantum photonic
integrated circuits,
quantum network

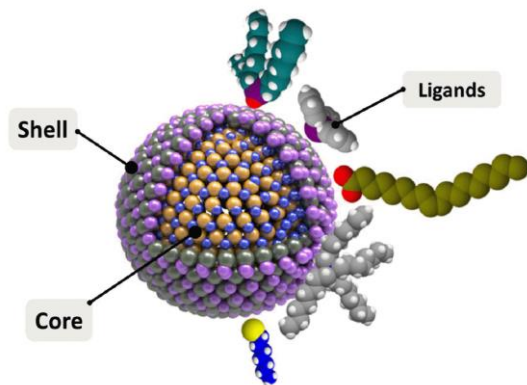


**Rb vapour cell
as a quantum
memory**



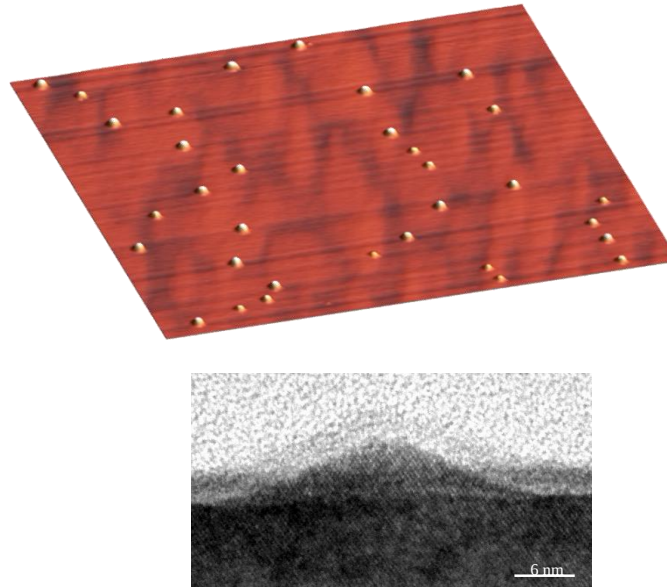
Synthesis of colloidal QDs

- Powder / in a liquid
- + Mass production
- Contacts (ligands)
- Optical instability (blinking)



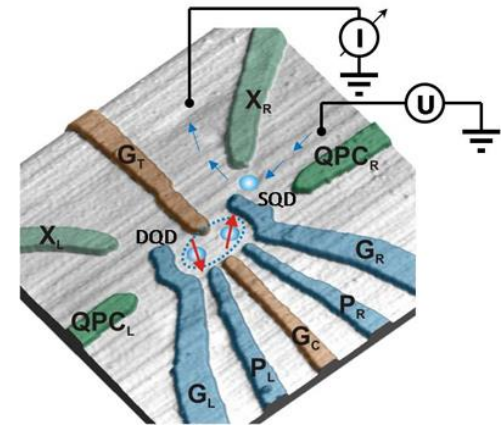
Self-assembly of epitaxial QDs

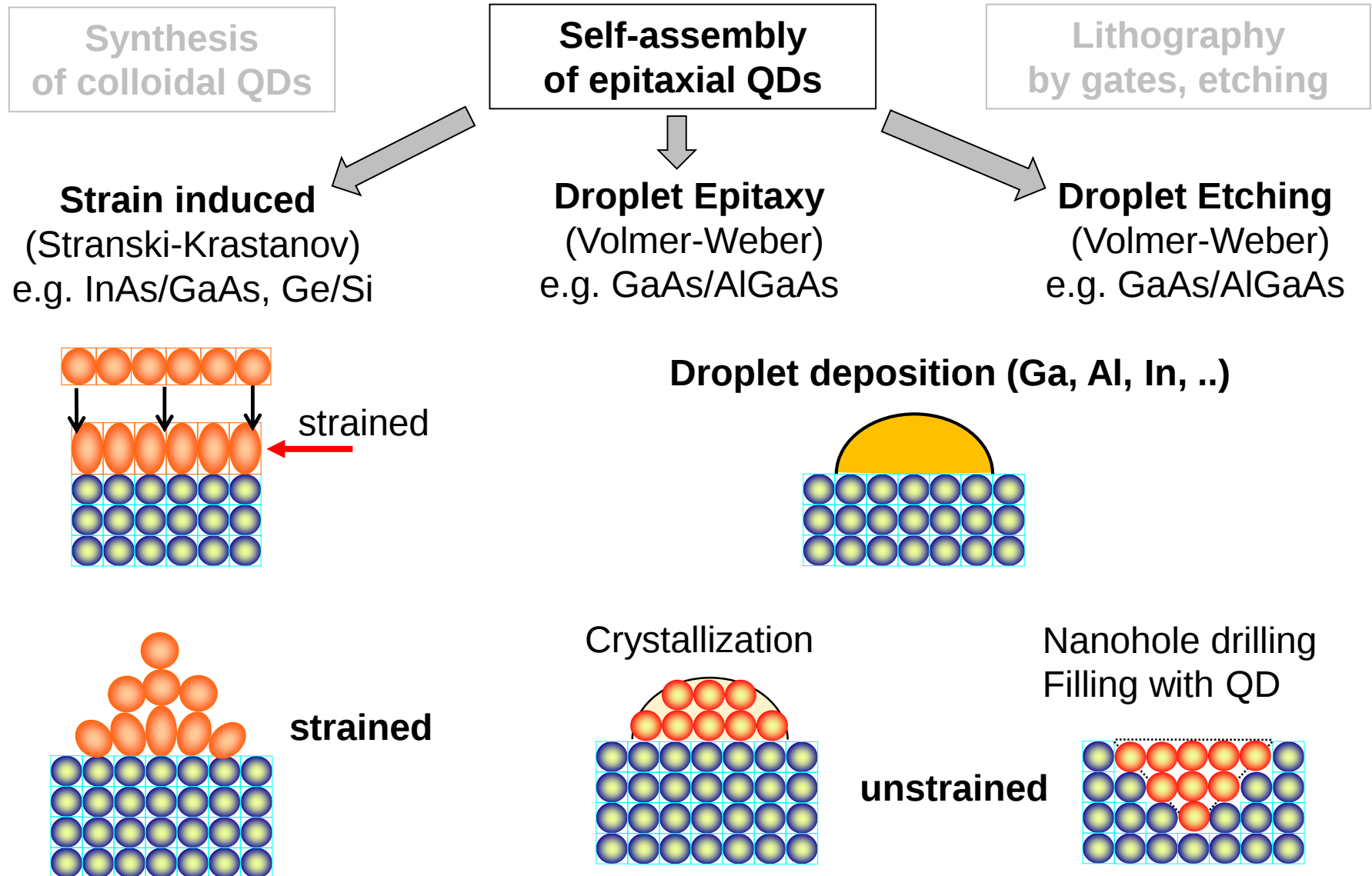
- Wafer based
- + Tunable density
- + Contacts
- + Optically stable



Lithography by gates, etching

- Wafer based
- + Single QDs
- + Contacts
- Optical emission





Synthesis
of colloidal QDs

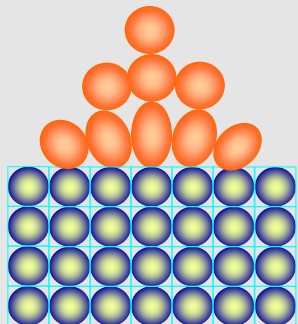
Self-assembly
of epitaxial QDs

Lithography
by gates, etching

Strain induced
(Stranski-Krastanov)

InAs/GaAs

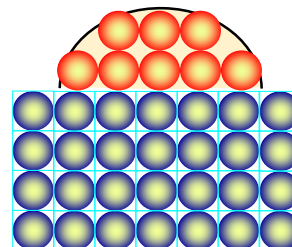
Emission: 1-1.3 μm



strained

Droplet Epitaxy
(Volmer-Weber)
e.g. GaAs/AlGaAs

Crystallization



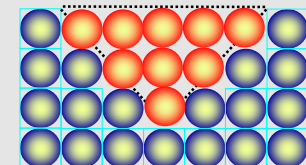
unstrained

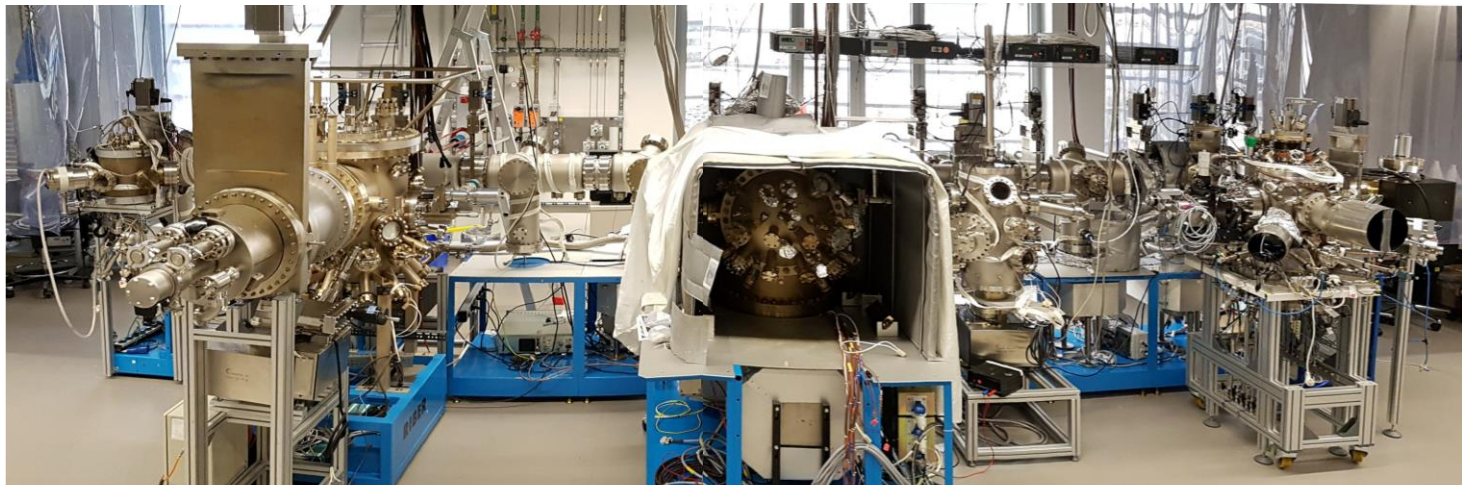
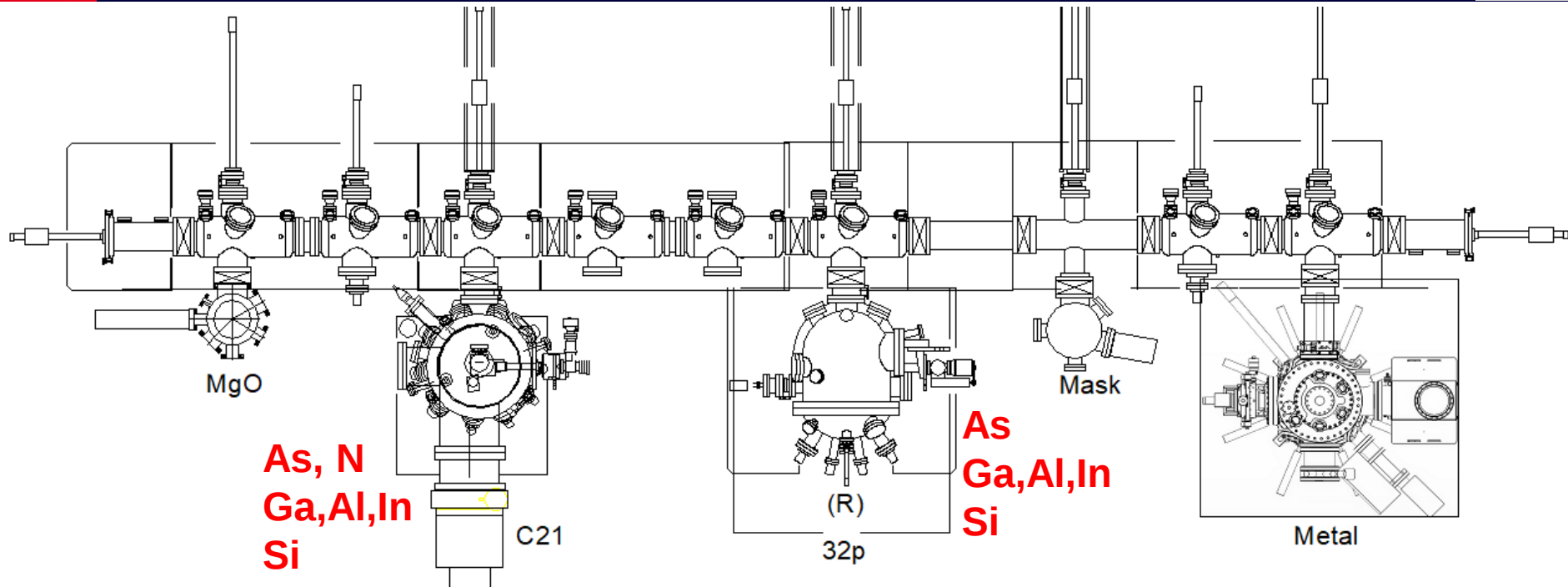
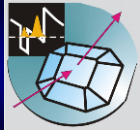
Droplet Etching
(Volmer-Weber)

GaAs/AlGaAs

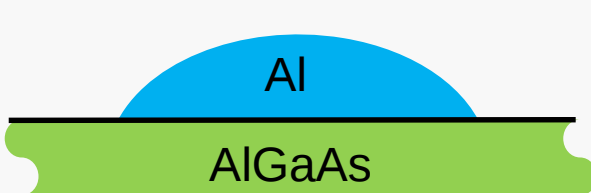
Emission: 680-810 nm

Nanohole drilling
Filling with QD

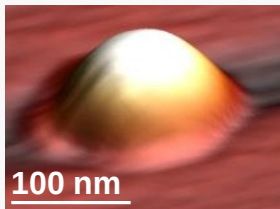




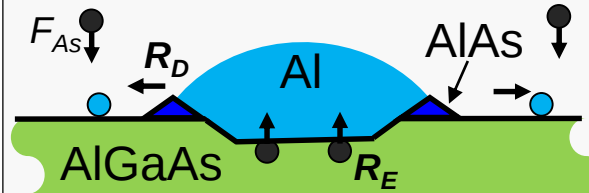
Droplet deposition



Minimization
of surface/
interface-
energies



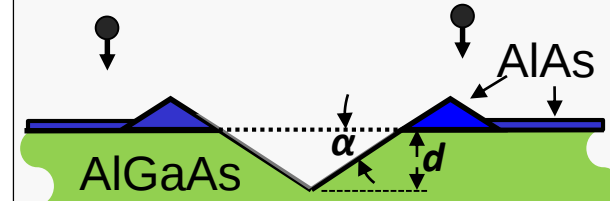
Annealing (early stage)



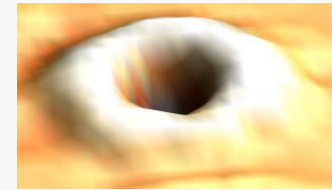
Etching,
formation of
crystalline
wall



Annealing ($\cong 100$ s)

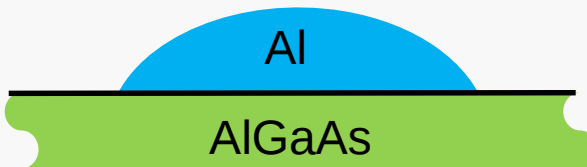


Droplet
material
removal

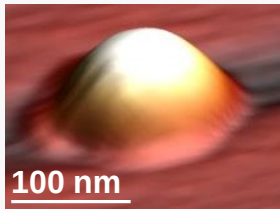


- Hole density:
 $2 \times 10^6 - 2 \times 10^9 \text{ cm}^{-2}$
- Hole depth:
2 - 120 nm

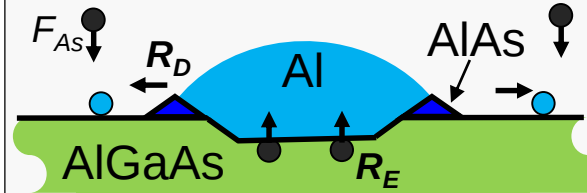
Droplet nucleation



Minimization
of surface/
interface-
energies



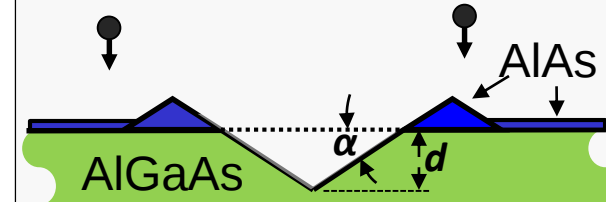
Annealing (early stage)



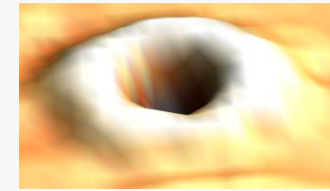
Etching,
formation of
crystalline
wall



Annealing ($\cong 100$ s)

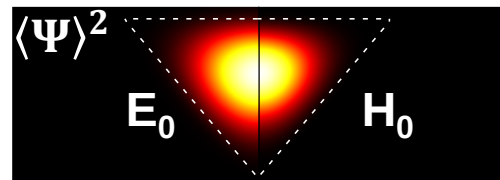
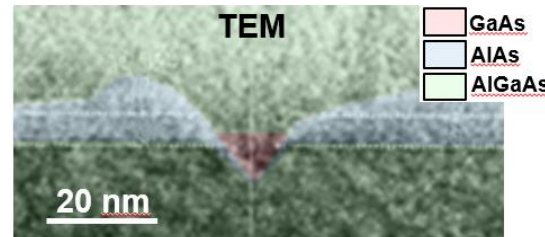


Droplet
material
removal

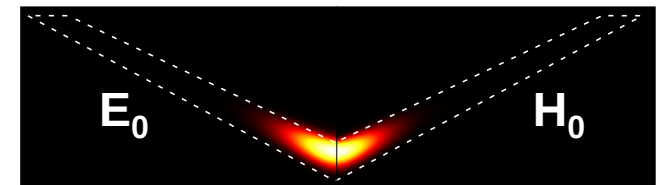
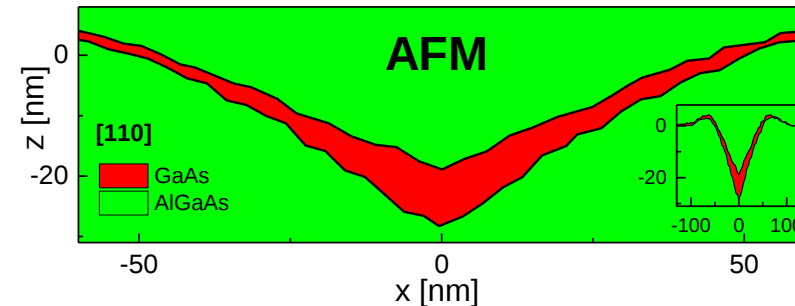


- Hole density:
 $2 \times 10^6 - 2 \times 10^9 \text{ cm}^{-2}$
- Hole depth:
2 - 120 nm
- **Hole filling:** highly
uniform QDs, size
controlled by filling
- QD shape controlled
by hole template

Cone QDs Sphere like $\langle \Psi \rangle^2$



Cone-shell QDs Disk like $\langle \Psi \rangle^2$



Low excitation: exciton lines
(linewidth down to 25 μeV)

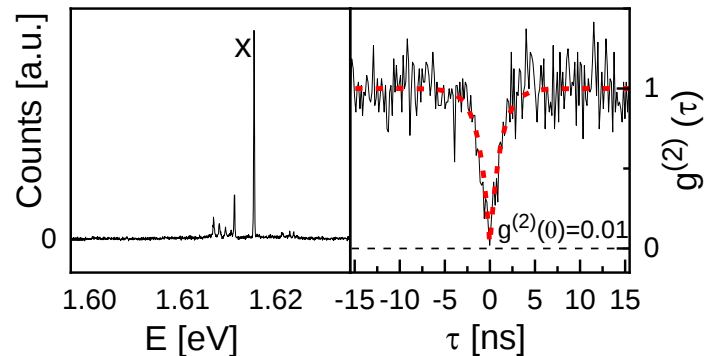
High excitation: shell structure
[Ch. Heyn et al., APL 94 (2009)]

Emission wavelength controlled by hole filling d_F : 680 - 810 nm

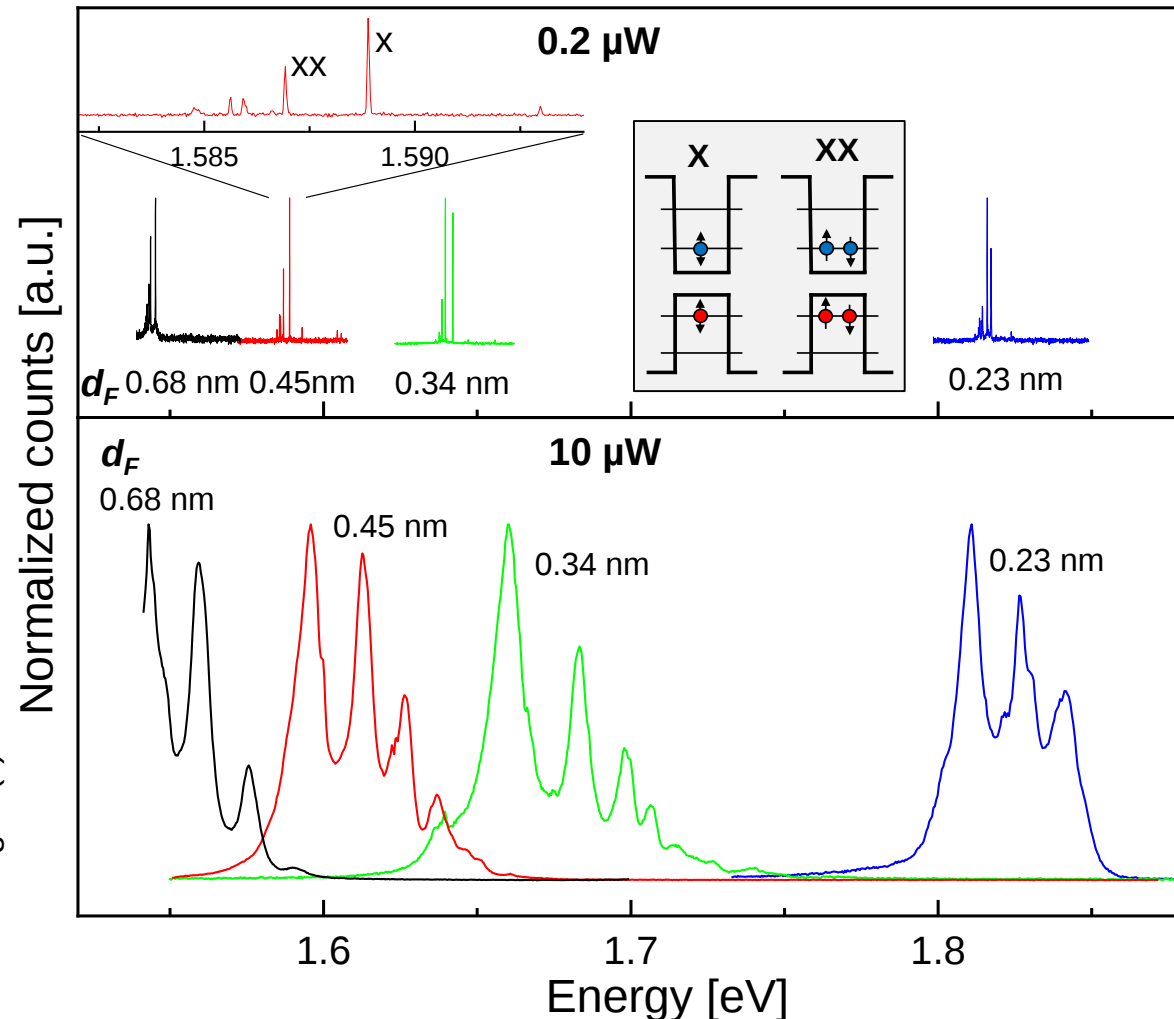
Exciton lifetime: 400 – 800 ps
[Ch. Heyn et al., N. J. Physics 14 (2012)]

Fine-structure splitting: 4.5 μeV

Single-photon emission
 $g^{(2)}(0)$: 0.01
[A. Küster et. al., Nanoscale Res. Lett. 11 (2016)]

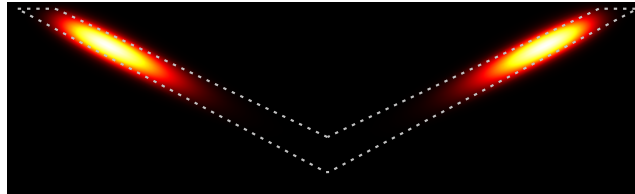


Single-dot photolumineszenz, $T = 8\text{K}$, cone-shell QDs
Varied excitation power and filling layer thickness d_F

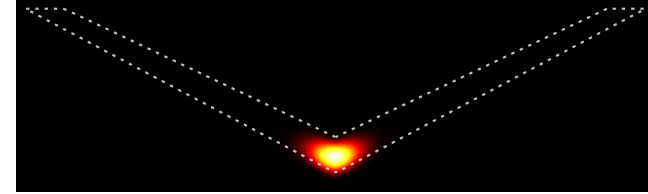


Vertical
electric field
 $F = -30\text{kV/cm}$

Electron, $\Psi_{e,0}^2$

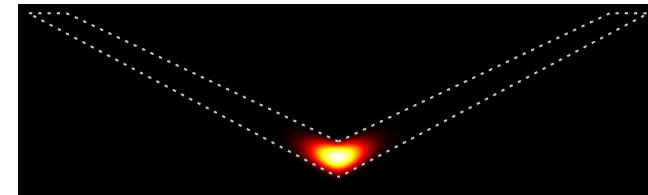
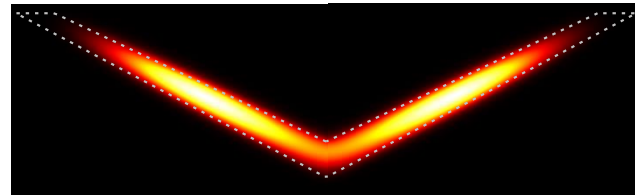


Hole, $\Psi_{h,0}^2$



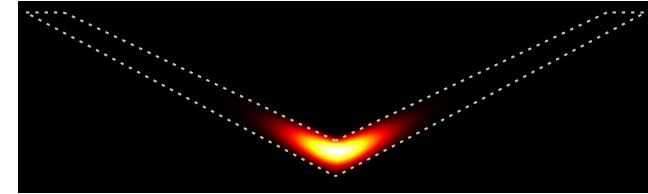
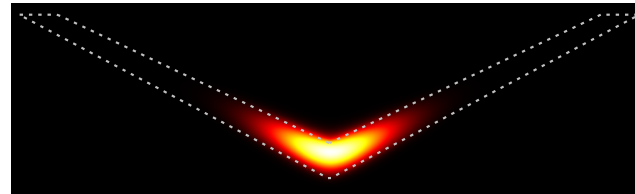
Ring e

$F = -20\text{kV/cm}$



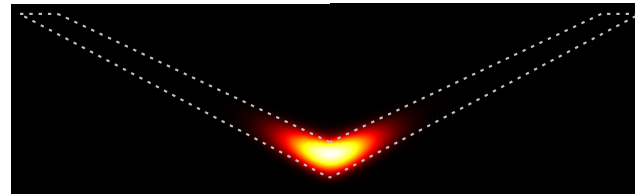
Dot

$F = 0$



Ring h

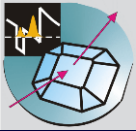
$F = 20\text{kV/cm}$



Simulations:

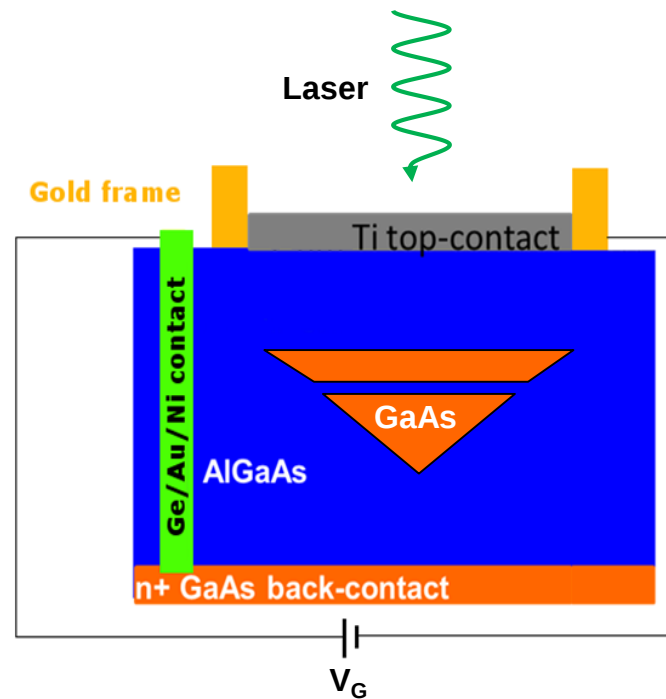
[Ch. Heyn et al., *phys. stat. sol. RRL* (2018)]

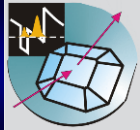
- Field-controlled dot to ring transition of either electron or hole
- Elongation of radiative lifetime up to milliseconds → quantum memory?



- Vertically self-aligned
(2 QDs and barrier in a nanohole)
- Adjustable QD sizes and barrier thickness
- Energy-state tuning via a vertical electric field by gate voltage V_G

[D. Sonnenberg et al., *Nanoscale* 6 (2014)]

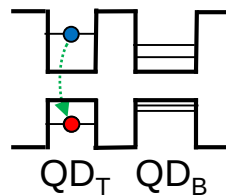




- Direct X and indirect excitons iX
- Anticrossing: **delocalized molecule states** (either symmetric or antisymmetric)
→ strong coupling
- Simulations of X, iX, anticrossing

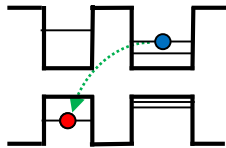
Small Stark-shift
(small QD_T height)

Direct exciton, X



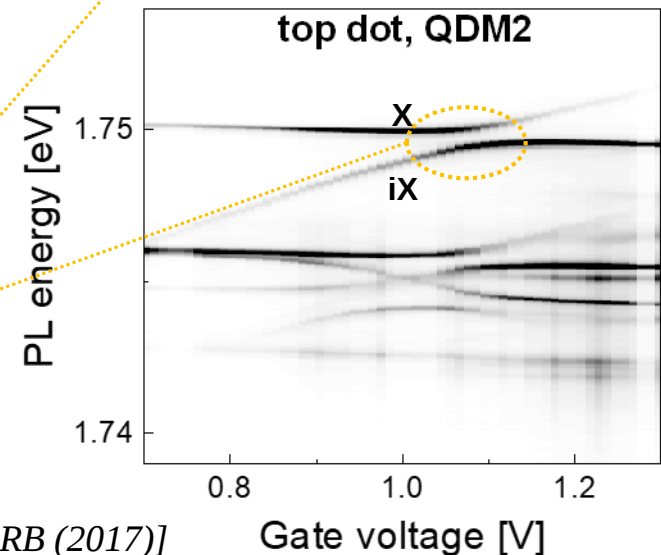
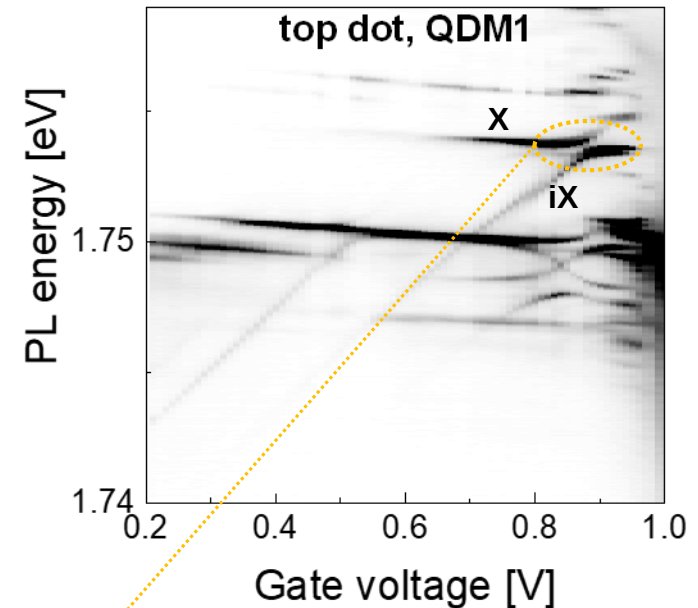
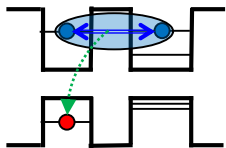
Strong field dependence
(large $QD_T - QD_B$ distance)
blue-shift: $h - QD_T$, $e - QD_B$

Indirect exciton, iX

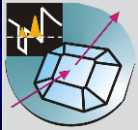


Resonance
(delocalization due to tunneling)

Anti-crossing



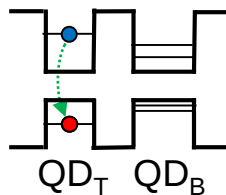
[Ch. Heyn et al., PRB (2017)]



- Direct X and indirect excitons iX
- Anticrossing: **delocalized molecule states** (either symmetric or antisymmetric)
→ strong coupling
- Simulations of X, iX, anticrossing

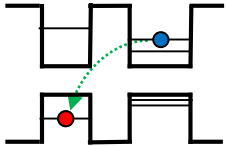
Small Stark-shift
(small QD_T height)

Direct exciton, X



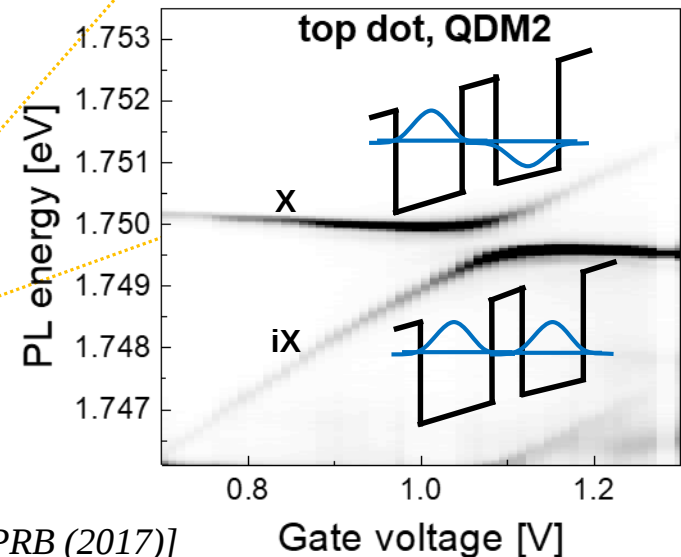
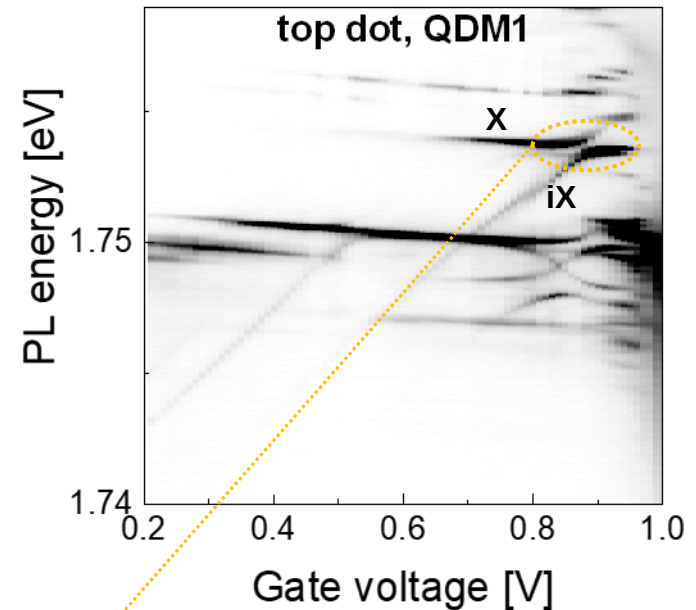
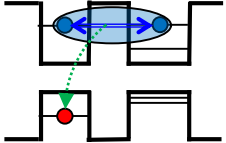
Strong field dependence
(large $QD_T - QD_B$ distance)
blue-shift: $h - QD_T$, $e - QD_B$

Indirect exciton, iX



Resonance
(delocalization due to tunneling)

Anti-crossing



[Ch. Heyn et al., PRB (2017)]

- **Epitaxial QDs:**

Deterministic source of single and entangled photons
Wide range of applications in photonic quantum technology

- **QDs by droplet etching**

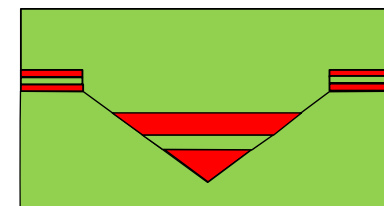
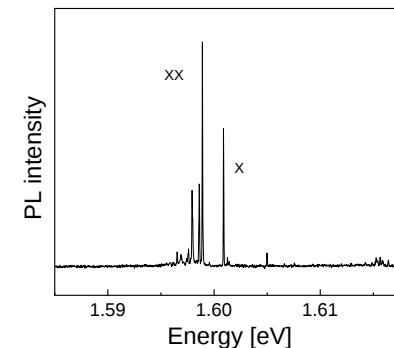
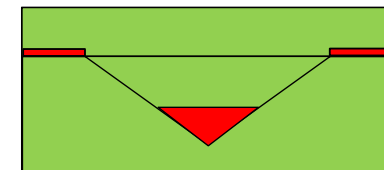
Morphology: strain-free, low density, size+shape tunable
Single-dot PL: sharp exciton lines, tunable wave length,
single-photon emission
Tunable wave function → quantum rings, ms lifetime

- **QD molecules**

Molecule-resonant electron states → strong coupling

- **Outlook**

Hybrid with Rb quantum memory, site-control, integration
into photonic environment, ...



HA 2042/6+8, HE 2644/2-1

Deutsche
Forschungsgemeinschaft

4PHOTON



RESEARCH & INNOVATION

Marie Skłodowska-Curie actions